

INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete if Known	
				Application Number	
				Filing Date	Concurrently Herewith
				First Named Inventor	Joseph J. Nahas
				Group Art Unit	
Examiner Name					
Sheet	1	of	1	Attorney Docket Number	
				SC13159TC	

U. S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number -Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
JS	AA	5,867,405	02/02/1999	Jiang <i>et al.</i>	
JS	AB	2002/0141232 A1	10/03/2002	Saito <i>et al.</i>	
JS	AO	6,545,906 B1	04/08/2003	Savtchenko <i>et al.</i>	

FOREIGN PATENT DOCUMENTS						
Examine Initials*	Cite No. ¹	Foreign Patent Document Country Code ³ Number ⁴ Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
JS	AC	Bae <i>et al.</i> , "Fabrication and Thermal-Chemical Stability of Magnetoresistive Random-Access Memory Cells Using α -Fe ₂ O ₃ Bottom Spin Values," <i>IEEE Transactions on Magnetism</i> , Vol. 37, No. 6, November 2001, pp. 3960-3968.	
JS	AD	Cheung, "Direct Charging Charge Device Model Testing of Magnetoresistive Recording Heads," <i>EOS/ESD Symposium</i> 97-398, 1997, pp. 398-404.	
JS	AE	M. Durlam, <i>et al.</i> , "A Low Power 1Mbit MRAM Based on 1T1MTJ Bit Cell Integrated with Copper Interconnects," <i>Symposium on VLSI Circuits Digest of Technical Papers</i> , 2002, pp. 158-161.	
JS	AF	B. A. Everitt <i>et al.</i> , "Single-Domain Model for Pseudo Spin Valve MRAM Cells," <i>IEEE Transactions on Magnetism</i> , September 1997, p. 3289-3291, Vol. 33, No. 5.	
JS	AG	P. K. George <i>et al.</i> , "Head Parameter Sensitivity Study of the Intrinsic Field Reversal Time," <i>Journal of Applied Physics</i> , April 15, 1999, p. 4979-4981, Vol. 85, No. 8.	
JS	AH	J. Mahdavi <i>et al.</i> , "Dynamic Modeling of Non-Linear SRM Drive with PSPICE," <i>IEEE Industry Applications Society Annual Meeting</i> , New Orleans, Louisiana, October 5-9, 1997, pp. 661-667.	
JS	AI	A. Maxim <i>et al.</i> , "A New Analog Behavioral SPICE Macromodel of Magnetic Components," <i>IEEE International Symposium on Industrial Electronics</i> , Guimarães, Portugal, University of Minho, July 7-11, 1997, pp. 183-188, Vol. 2 of 3.	
JS	AJ	A. Maxim <i>et al.</i> , "A Novel Behavioral Method of SPICE Macromodeling of Magnetic Components Including the Temperature and Frequency Dependencies," <i>IEEE Power Electronics Conference</i> , 1998, pp. 393-399.	
JS	AK	T. Sugawara <i>et al.</i> , "A Nonlinear Model for Magnetic Recording Channel with an MR Head," <i>IEEE Transactions on Magnetism</i> , January 1998, p. 57-62, Vol. 34, No. 1.	
JS	AL	A. Wallash, "Field-Induced Charged Device Model Testing of Magnetoresistive Recording Heads," <i>EOS/ESD Symposium</i> , 1996, pp. 8-13.	
JS	AM	A. Wallash <i>et al.</i> , "ESD Evaluation of Tunneling Magnetoresistive (TMR) Devices," <i>EOS/ESD Symposium</i> , 2000, pp. 470-474.	
JS	AN	U.S. Patent Application 10/302,203 filed November 22, 2002, entitled "Method and Apparatus for Simulating a Magnetoresistive Random Access Memory (MRAM)", assignee same as assignee hereof.	

Examiner Signature		Date Considered	12/12/05
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